
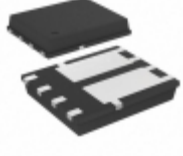
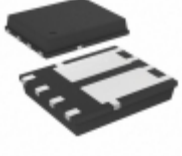
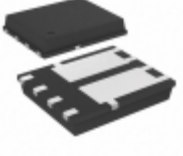

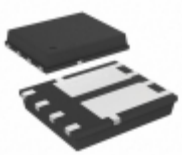
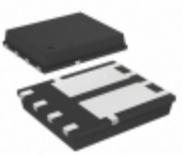
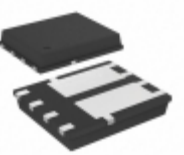
	<h2>SI7960DP-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7960DP-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET 2N-CH 60V 6.2A PPAK SO-8</p> <p>Datenblätter:  SI7960DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 798200 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7960DP-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET 2N-CH 60V 6.2A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	798200 pcs Stock
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.4W
Verpackung / Gehäuse	PowerPAK® SO-8 Dual
Supplier Device-Gehäuse	PowerPAK® SO-8 Dual
Typ FET	2 N-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	6.2A
Rds On (Max) @ Id, Vgs	21 mOhm @ 9.7A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	75nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)


























SI7960DP-T1-GE3 ist neu im Original, Suche SI7960DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7960DP-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7960DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7960DP-T1-E3 Vishay / Siliconix MOSFET 2N-CH 60V 6.2A PPAK SO-8</p>	 <p>SI7962DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 40V 7.1A PPAK SO-8</p>	 <p>SI7962DP-T1-E3 Vishay / Siliconix MOSFET 2N-CH 40V 7.1A PPAK SO-8</p>	 <p>SI7964DP V V SI7964DP V</p>
 <p>SI7960DP SI SI SI7960DP SI</p>	 <p>SI7960DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 60V 6.2A PPAK SO-8</p>	 <p>SI7960DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 60V 6.2A PPAK SO-8</p>	 <p>SI7964DP-T1-E3 Vishay / Siliconix MOSFET 2N-CH 60V 6.1A PPAK SO-8</p>

heiße Teile

Mehr

 SI7922DN-T1-GE3	 SI7922DN-T1-GE3	 SI7923DN-T1-E3	 SI7923DN-T1-E3	 SI7923DN-T1-GE3
 SI7923DN-T1-GE3	 SI7938DP-T1-GE3	 SI7938DP-T1-GE3	 SI7940DP	 SI7940DP-T1-E3
 SI7940DP-T1-E3	 SI7941DP-T1-E3	 SI7941DP-T1-GE3	 SI7942DP	 SI7942DP-T1-E3
 SI7942DP-T1-E3	 SI7942DP-T1-GE3	 SI7942DP-T1-GE3	 SI7945DP-T1-E3	 SI7945DP-T1-E3
 SI7946DP	 SI7946DP-T1-E3	 SI7946DP-T1-E3	 SI7948DP	 SI7948DP-T1-E3
 SI7949DP-T1-GE3	 SI7949DP-T1-GE3	 SI7956DP-T1-GE3	 SI7956DP-T1-GE3	 SI7958DP
 SI7958DP-T1-E3	 SI7958DP-T1-E3	 SI7958DP-T1-GE3	 SI7958DP-T1-GE3	 SI7960DP-T1-E3
 SI7960DP-T1-E3	 SI7960DP-T1-GE3	 SI7964DP	 SI7964DP-T1-GE3	 SI7964DP-T1-GE3
 SI7970DP	 SI7970DP-T1-E3	 SI7980DP-T1-E3	 SI7980DP-T1-E3	 SI7980DP-T1-GE3
 SI7980DP-T1-GE3	 SI7997DP-T1-GE3	 SI7997DP-T1-GE3	 SI7998DP-T1-GE3	 SI7998DP-T1-GE3

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